

GL4403

PNP EPITAXIAL PLANAR TRANSISTOR

Description

The GL4403 is designed for general purpose switching and amplifier applications.

Features

- Complementary to GL4401
- High Power Dissipation: 1500mW at 25°C
- High DC Current Gain: 100-300 at 150mA

Package Dimensions

SOT-223

Marking :

Date Code →

REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	6.70	7.30	B	13 TYP.	
C	2.90	3.10	J	2.30 REF.	
D	0.02	0.10	1	6.30	6.70
E	0°	10°	2	6.30	6.70
I	0.60	0.80	3	3.30	3.70
H	0.25	0.35	4	3.30	3.70
			5	1.40	1.80

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Ratings	Unit
Junction Temperature	T _j	+150	°C
Storage Temperature	T _{stg}	-55 ~ +150	°C
Collector to Base Voltage at Ta=25°C	V _{CB0}	-40	V
Collector to Emitter Voltage at Ta=25°C	V _{CE0}	-40	V
Emitter to Base Voltage at Ta=25°C	V _{EB0}	-5	V
Collector Current at Ta=25°C	I _C	-600	mA
Total Power Dissipation at Ta=25°C	PD	1.5	W

Characteristics at Ta = 25°C

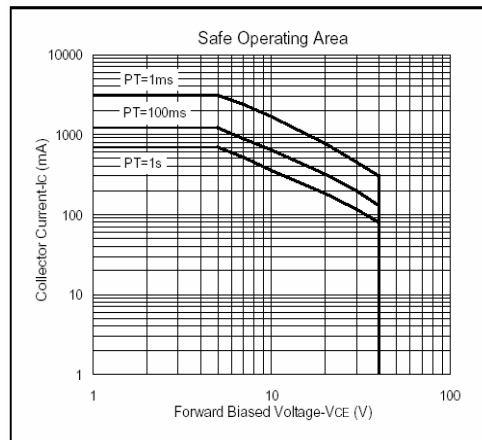
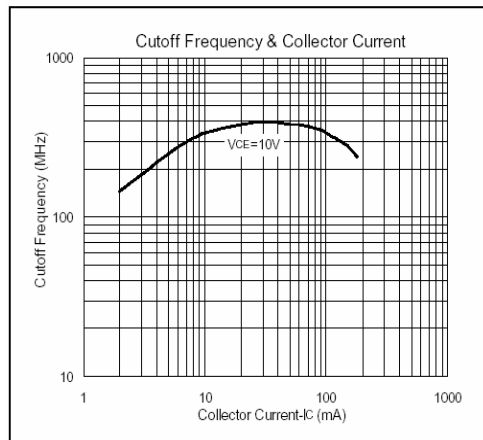
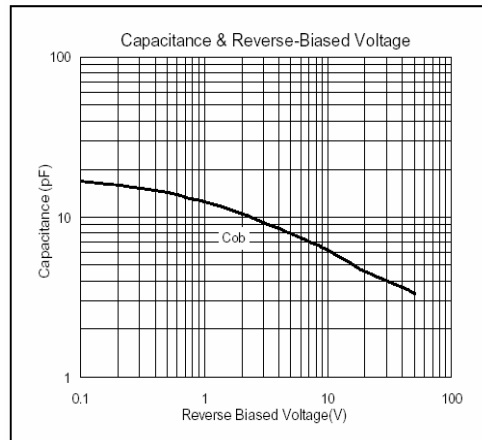
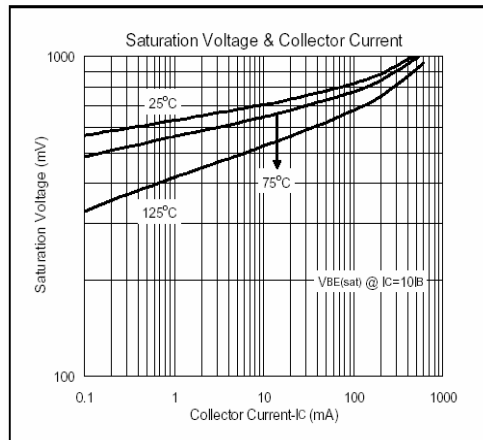
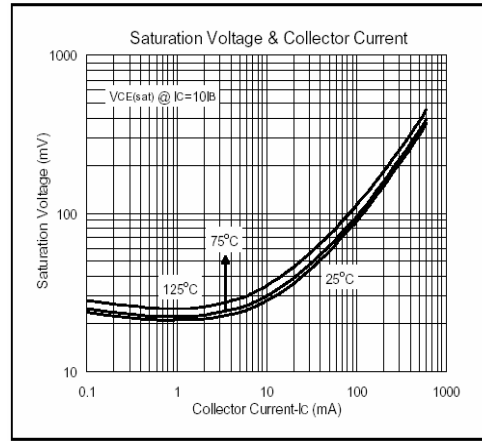
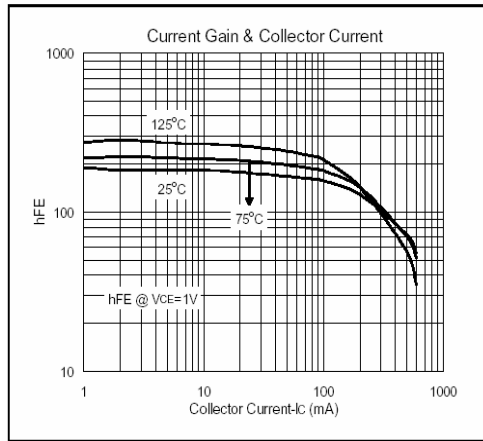
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV _{CB0}	-40	-	-	V	I _C =-100uA
BV _{CE0}	-40	-	-	V	I _C =-1mA
BV _{EB0}	-5	-	-	V	I _E =-10uA
ICE _X	-	-	-100	nA	V _{CE} =-35V, V _{BE} =-0.4V
*V _{CE(sat)1}	-	-	-400	mV	I _C =-150mA, I _B =-15mA
*V _{CE(sat)2}	-	-	-750	mV	I _C =-500mA, I _B =-50mA
*V _{BE(sat)1}	-750	-	-950	mV	I _C =-150mA, I _B =-15mA
*V _{BE(sat)2}	-	-	-1.3	V	I _C =-500mA, I _B =-50mA
*h _{FE1}	30	-	-		V _{CE} =-1V, I _C =-0.1mA
*h _{FE2}	60	-	-		V _{CE} =-1V, I _C =-1mA
*h _{FE3}	100	-	-		V _{CE} =-1V, I _C =-10mA
*h _{FE4}	100	-	300		V _{CE} =-2V, I _C =-150mA
*h _{FE5}	20	-	-		V _{CE} =-2V, I _C =-500mA
f _T	200	-	-	MHz	V _{CE} =-10V, I _C =-20mA, f=100MHz
C _{ob}	-	-	8.5	pF	V _{CE} =-10V, f=1MHz

Classification Of hFE4

Rank	A	B
Range	100-210	190-300

* Pulse Test: Pulse Width ≤ 380μs, Duty Cycle ≤ 2%

Characteristics Curve



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Head Office And Factory:

- **Taiwan:** No. 17-1 Tatung Rd. Fu Kou Hsin-Chu Industrial Park, Hsin-Chu, Taiwan, R. O. C.
TEL : 886-3-597-7061 FAX : 886-3-597-9220, 597-0785
- **China:** (201203) No.255, Jang-Jiang Tsai-Lueng RD. , Pu-Dung-Hsin District, Shang-Hai City, China
TEL : 86-21-5895-7671 ~ 4 FAX : 86-21-38950165